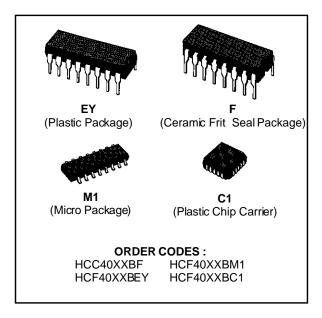


# HCC/HCF4049UB HCC/HCF4050B

### HEX BUFFER/CONVERTERS

#### 4049UB INVERTING TYPE 4050B NON-INVERTING TYPE

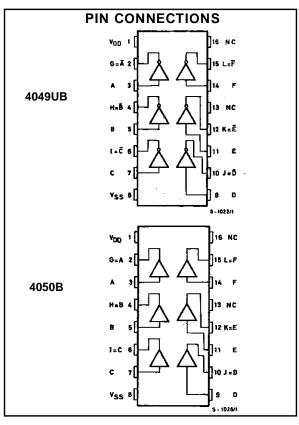
- HIGH SINK CURRENT FOR DRIVING 2 TTL LOADS
- HIGH-TO-LOW LEVEL LOGIC CONVERSION
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- HIGH "SINK" AND "SOURCE" CURRENT CA-PABILITY
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100 nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N°. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"



#### **DESCRIPTION**

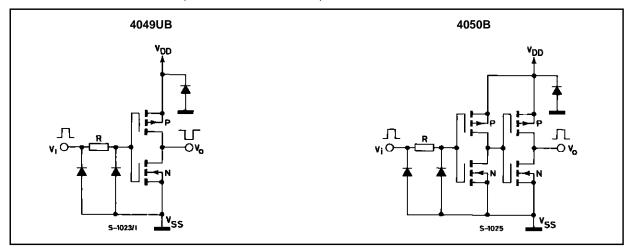
The **HCC4049UB/4050B** (extended temperature range) and the **HCF4049UB/4050B** (intermediate temperature range) are monolithic integrated circuits available in 16-lead dual in-line plastic or ceramic package and plastic micro package.

The **HCC/HCF4049UB/4050B** are inverting and non-inverting hex buffers, respectively, and feature logic-level conversion using only one supply voltage ( $V_{DD}$ ). The input-signal high level ( $V_{IH}$ ) can exceed the  $V_{DD}$  supply voltage when these devices are used for logic level conversions. These devices are intended for use as COS/MOS to DTL/TTL converters and can drive directly two DTL/TTL loads ( $V_{DD} = 5V$ ,  $V_{OL} \le 0.4V$ , and  $I_{OL} \ge 3.2\text{mA}$ ).



June 1989 1/12

#### SCHEMATIC DIAGRAMS (1 of 6 identical units)



#### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>DD</sub> *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V
$V_{i}$	Input Voltage	- 0.5 to V <sub>DD</sub> + 0.5	V
$I_1$	DC Input Current (any one input)	± 10	mA
P <sub>tot</sub>	Total Power Dissipation (per package) Dissipation per Output Transistor for $T_{op}$ = Full Package-temperature Range	200	mW mW
Top	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	°C
T <sub>stg</sub>	Storage Temperature	- 65 to + 150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

#### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Value	Unit
$V_{DD}$	Supply Voltage: HCC Types	3 to 18	V
	HCF Types	3 to 15	V
$V_{I}$	Input Voltage	0 to V <sub>DD</sub>	V
Top	Operating Temperature : HCC Types	- 55 to + 125 - 40 to + 85	ပ္ခဲ့
	HCF Types	- 40 t0 + 85	ر



<sup>\*</sup> All voltage values are referred to V<sub>SS</sub> pin voltage.

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

			Tes	t Conditi	ons				Value				
Symbol	Paramo	eter	V <sub>I</sub>	V <sub>1</sub> V <sub>2</sub> V <sub>DP</sub>	TL	* OW		25°C		T <sub>H</sub>	iah *	Unit	
•			(V) (V)	(V)	Min.	Max.	Min.	Тур.	Max.	Min.	Max.		
IL .	Quiescent		0/ 5		5		1		0.02	1		30	
-	Supply	нсс	0/10		10		2		0.02	2		60	
	Current	Types	0/15		15		4		0.02	4		120	
		''	0/20		20		20		0.04	20		600	
			0/ 5		5		4		0.02	4		30	μΑ
		HCF	0/10		10		8		0.02	8		60	
		Types	0/15		15		16		0.02	16		120	
V <sub>OH</sub>	Output Higl	h	0/ 5		5	4.95		4.95			4.95		
OH	Voltage		0/10		10	9.95		9.95			9.95		V
			0/15		15	14.95		14.95			14.95		•
V <sub>OL</sub>	Output Low	/	5/0		5	1	0.05			0.05		0.05	
- OL	Voltage		10/0		10		0.05			0.05		0.05	V
	J		15/0		15		0.05			0.05		0.05	V
V <sub>IH</sub>	Input High		10/0	0.5	5	4	0.00	4		0.00	4	0.00	
* IH	Voltage (40	)49UB)		1	10	8		8			8		V
		, , ,		2	15	12		12			12		⊢
V <sub>IH</sub>	Input High			4.5	5	3.5		3.5			3.5		
* IH	Voltage (40	)50B)		9	10	7		7			7		V
	i onago ( i o	,002,		13.5	16	11		11		<del>                                     </del>	11		─
V <sub>IL</sub>	Input Low	W		4.5	5	<del>  ''</del>	1	' '		1	- ' '	1	
		Voltage (4049UB)		9	10		2			2		2	V
	Tomago (10			13	15		3			3		3	,
V <sub>IL</sub>	Input Low			0.5	5		1.5			1.5		1.5	
۷IL	Voltage (40	150B)		1	10		3			3		3	V
	Voltage (40	,оов,		1.5	15		4			4		4	V
1	Output	1	0/ 5	2.5	5	1.6	4	-1.25	- 6.4	+	- 0.9	4	
l <sub>он</sub>	Output Drive		0/ 5	4.6	5	0.64		-0.51	- 6.4 - 1.6	-	-0.36		
	Current	HCC	0/ 5	9.5		1.6					-0.3 <del>6</del>		
	Curon	Types			10	4.7		-1.30					
			0/15	13.5	15	1.5		-3.75		-	- 2.7 - 1		A
			0/ 5	2.5	5			-1.25					mA
		HCF	0/ 5	4.6	5	0.61		-0.51	- 1.6		-0.42		
		Types	0/10	9.5	10	1.5		-1.25		-	- 1		
	0		0/15	13.5	15	4.5		-3.75	- 12		- 3		
$I_{OL}$	Output	нсс	0/ 5	0.4	5	3.75		3.2	6.4		2.2	$\vdash \vdash \vdash$	
	Sink	Types	0/10	0.5	10	10		8	16		5.6	$\vdash \vdash \vdash$	
	Juneni	<u> </u>	0/15	1.5	15	30		24	48		17	$\vdash$	mΑ
		HCF	0/ 5	0.4	5	3.6		3.2	6.4		2.6		
		Types	0/10	0.5	10	9.6		8	16		6.6	igwdown	_
_			0/15	1.5	15	28		24	48		19		
I <sub>IH</sub> , I <sub>IL</sub>	Input Leakage	HCC Types	0/18		18		± 0.1		±10 <sup>-5</sup>	± 0.1		± 1	μΑ
	Current	HCF Types	0/15		15		± 0.3		±10 <sup>-5</sup>			± 1	•
Cı	Input Capacitance	4049UB 4050B		Any Input					15 5	22.5 7.5			pF

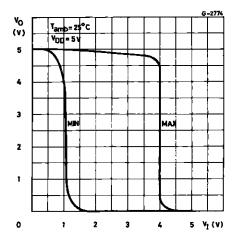
<sup>(\*)</sup>  $T_{Low} = -55^{\circ}\text{C}$  for HCC device :  $-40^{\circ}\text{C}$  for HCF device.  $T_{High} = +125^{\circ}\text{C}$  for HCC device :  $+85^{\circ}\text{C}$  for HCF device. The Noise Margin (only HCC/HCF4050B type) for both "1" and "0" level is : 1V min. with  $V_{DD} = 5V$ , 2V min. with  $V_{DD} = 10V$ , 2.5V min. with  $V_{DD}$  = 15V.



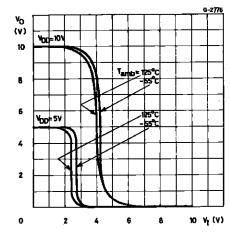
**DYNAMIC ELECTRICAL CHARACTERISTICS** ( $T_{amb} = 25^{\circ}C$ ,  $C_{L} = 50 pF$ ,  $R_{L} = 200 k\Omega$ , typical temperature coefficient for all  $V_{DD}$  values is  $0.3\%/^{\circ}C$ , all input rise and fall times = 20ns)

0	Barrantan	Test Cond	lition						
Symbol	Parameter	V <sub>I</sub>	(V)	$V_{DD}$ (V)	Min.	Тур.	Max.	Unit	
t <sub>PLH</sub>	Propagation Delay Time		5	5		60	120		
	(4049UB)	1	10	10		32	65		
		1	10	5		45	90	ns	
		1	15	15		25	50		
		1	15	5		45	90		
t <sub>PLH</sub>	Propagation Delay Time		5	5		70	140		
	(4050B)	1	10	10		40	80		
		1	10	5		45	90		
		1	15	15		30	60		
		1	15	5		40	80		
t <sub>PHL</sub>	Propagation delay Time (4049UB)		5	5		32	65	ns	
		1	10	10		20	40		
		1	10	5		15	30		
		1	15	15		15	30		
		1	15	5		10	20		
t <sub>PHL</sub>	Propagation Delay Time		5	5		55	110		
	(4050B)	1	10	10		22	55		
		1	10	5		50	100	ns	
		1	15	15		15	30		
		1	15	5		50	100		
t <sub>TLH</sub>	Transition Time		5	5		80	160		
		1	10	10		40	80		
		1	15	15		30	60	ns	
t <sub>THL</sub>	Transition Time		5	5		30	60	115	
		1	10	10		20	40		
		1	15	15		15	30		

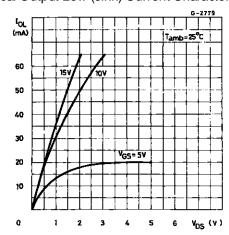
Minimum and Maximum Voltage Transfer Characteristics for 4049UB.



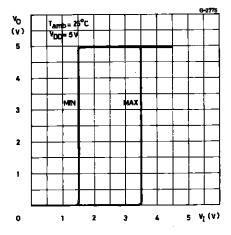
Typical Voltage Transfer Characteristics as a Function of Temperature for 4049UB.



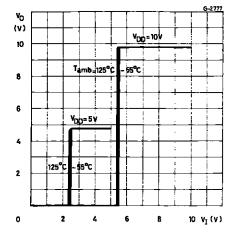
Typical Output Low (sink) Current Characteristics.



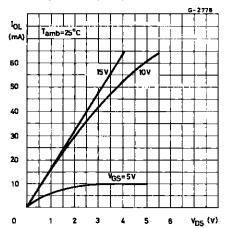
Minimum and Maximum Voltage Transfer Characteristics for 4050B.



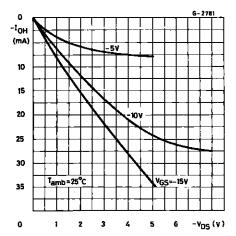
Typical Voltage Transfer Characteristics as a Function of Temperature for 4050B.



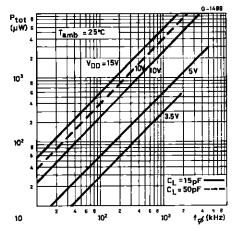
Minimum Output Low (sink) Current Characteristics.



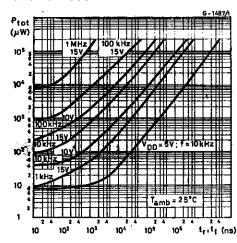
Typical Output High (source) Current Characteristics.



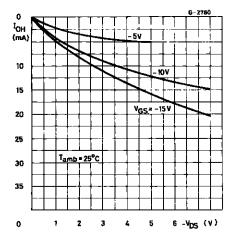
Typical Power Dissipation per Buffer/Inverter vs. Frequency.



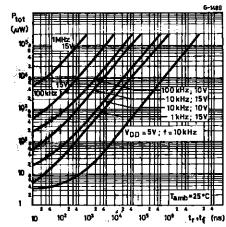
Typical Power Dissipation vs. Input Transition Time per Inverter for 4050B.



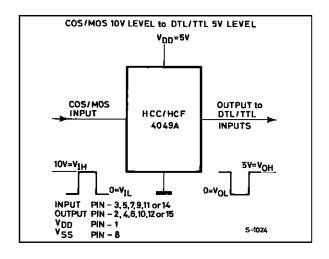
Minimum Output High (source) Current Characteristics.



Typical Power Dissipation vs. Input Transition Time per Inverter for 4049UB.

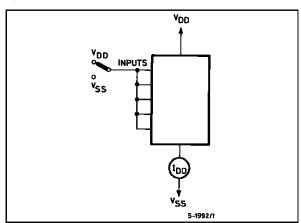


Logic-Level Conversion Application.

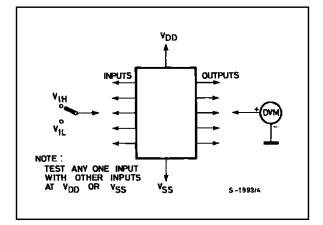


#### **TEST CIRCUITS**

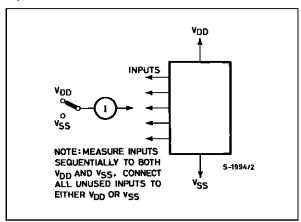
Quiescent Device Current.



Input Voltage.

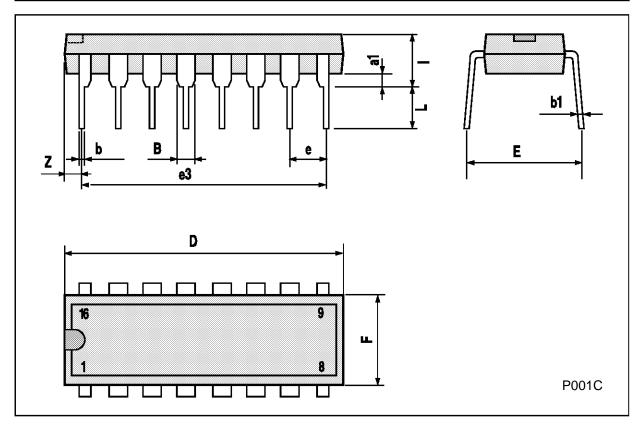


Input Current.



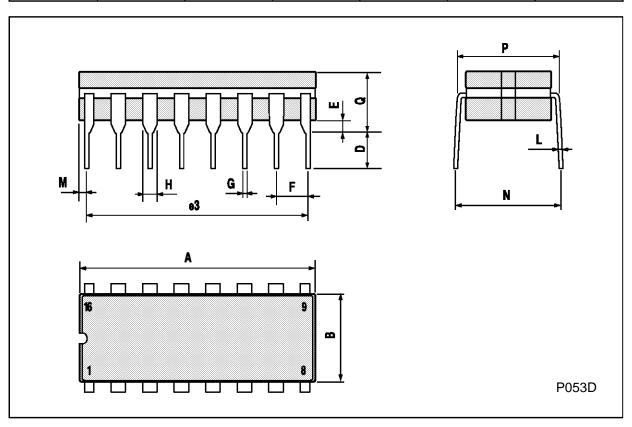
# Plastic DIP16 (0.25) MECHANICAL DATA

DIM.		mm			inch	
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
В	0.77		1.65	0.030		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
е		2.54			0.100	
e3		17.78			0.700	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z			1.27			0.050



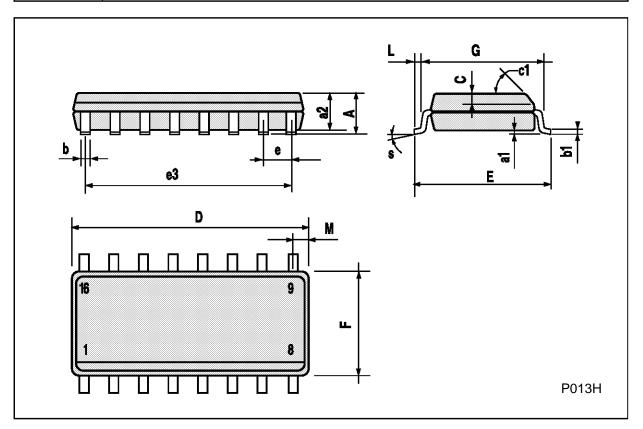
## **Ceramic DIP16/1 MECHANICAL DATA**

DIM.		mm			inch	
J	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А			20			0.787
В			7			0.276
D		3.3			0.130	
Е	0.38			0.015		
e3		17.78			0.700	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
Н	1.17		1.52	0.046		0.060
L	0.22		0.31	0.009		0.012
М	0.51		1.27	0.020		0.050
N			10.3			0.406
Р	7.8		8.05	0.307		0.317
Q			5.08			0.200



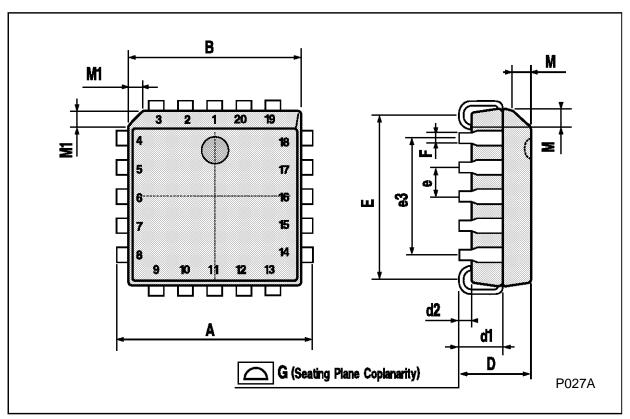
# SO16 (Narrow) MECHANICAL DATA

DIM.		mm			inch	
Dilvi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А			1.75			0.068
a1	0.1		0.2	0.004		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
С		0.5			0.019	
c1			45°	(typ.)		
D	9.8		10	0.385		0.393
Е	5.8		6.2	0.228		0.244
е		1.27			0.050	
e3		8.89			0.350	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
М			0.62			0.024
S			8° (r	nax.)		



### **PLCC20 MECHANICAL DATA**

DIM.		mm			inch	
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	9.78		10.03	0.385		0.395
В	8.89		9.04	0.350		0.356
D	4.2		4.57	0.165		0.180
d1		2.54			0.100	
d2		0.56			0.022	
E	7.37		8.38	0.290		0.330
е		1.27			0.050	
e3		5.08			0.200	
F		0.38			0.015	
G			0.101			0.004
М		1.27			0.050	
M1		1.14			0.045	



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